TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $L^2$ - $\pi$ -MOSV)

# 2SK3205

# Switching Regulator Applications DC-DC Converter, and Motor Drive Applications

4 V gate drive

 $\begin{array}{ll} \bullet & Low \ drain-source \ ON \ resistance & : RDS \ (ON) = 0.36 \ \Omega \ (typ.) \\ \bullet & High \ forward \ transfer \ admittance & : | Y_{fs}| = 4.5 \ S \ (typ.) \\ \bullet & Low \ leakage \ current & : I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 150 \ V) \\ \bullet & Enhancement-mode & : V_{th} = 0.8 \sim 2.0 \ V \ (V_{DS} = 10 \ V, \ I_D = 1 \ mA) \\ \end{array}$ 

#### **Absolute Maximum Ratings (Ta = 25°C)**

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	150	V	
Drain-gate voltage (Ro	<sub>GS</sub> = 20 kΩ)	V <sub>DGR</sub>	150	V	
Gate-source voltage		$V_{GSS}$	±20	V	
Drain current	DC (Note 1)	ΙD	5	Α	
	Pulse (Note 1)	$I_{DP}$	20	^	
Drain power dissipation	n (Tc = 25°C)	PD	20	W	
Single pulse avalanche	e energy (Note 2)	E <sub>AS</sub>	71	mJ	
Avalanche current		I <sub>AR</sub>	5	Α	
Repetitive avalanche e	nergy (Note 3)	E <sub>AR</sub>	2	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	6.25	°C / W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	125	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

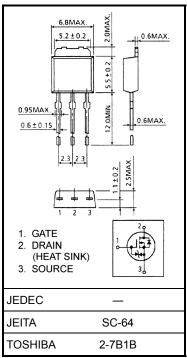
Note 2:  $V_{DD}$  = 50 V,  $T_{ch}$  = 25°C (initial), L = 4.2 mH,  $I_{AR}$  = 5 A,  $R_G$  = 25  $\Omega$ 

Note 3: Repetitive rating; Pulse width limited by maximum channel temperature.

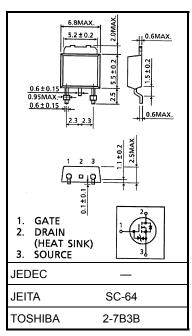
This transistor is an electrostatic sensitive device.

Please handle with caution.

Unit: mm



Weight: 0.36 g (typ.)



Weight: 0.36 g (typ.)



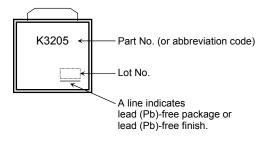
## **Electrical Characteristics (Ta = 25°C)**

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V		_	±10	μΑ
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V	_	_	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	150	_	_	V
Gate threshold v	oltage/	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	0.8	_	2.0	٧
Drain-source ON resistance		R <sub>DS (ON)</sub>	V <sub>GS</sub> = 4 V, I <sub>D</sub> = 2.5 A	I	0.54	0.75	Ω
		R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.5 A	_	0.36	0.5	
Forward transfer	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 2.5 A	2.0	4.5	_	S
Input capacitance		C <sub>iss</sub>		_	330	_	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	50	_	pF
Output capacitance		Coss		_	145	_	
Switching time	Rise time	tr	$V_{\rm GS}$ $^{10V}_{\rm OV}$ $^{\rm I}_{\rm D}$ $^{\rm I}_{\rm D}$ $^{\rm OV}_{\rm OUT}$ $^{\rm R}_{\rm L}$ $^{\rm R}_{\rm L}$ $^{\rm R}_{\rm L}$	_	10	_	ns
	Turn-on time	t <sub>on</sub>		_	15	_	
	Fall time	t <sub>f</sub>		_	10	_	
	Turn-off time	t <sub>off</sub>	$V_{DD} = 100V$ Duty $\leq 1\%$ , $t_w = 10\mu s$	_	60	_	
Total gate charge (Gate-source plus gate-drain)		Qg			12		
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 120 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$		8		nC
Gate-drain ("miller") charge		Q <sub>gd</sub>		_	4		

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>		_	_	5	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>		_	_	20	Α
Forward voltage (diode)	$V_{DSF}$	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V, dI <sub>DR</sub> / dt = 100 A / μs	1	110	1	ns
Reverse recovery charge	Qrr	IDR = 3 A, VGS = 0 V, αIDR / αt = 100 A / μs	1	0.47	-	nC

## Marking



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